## Appikation Number: 19723,046 (Porg et al.) An Unit 2311 Amendment continued

CLAIMS: Piease amend the claims according to the stows designations in the following list, which contains oil claims that were over in the patent application, with the text of all active theory.

## Wreat I claim are:

- (Chrenty emended) A secienadector device, comprising
- a substrate with lexture on the top surface of said substrate, and
- an epitaxial layor comprising an active layer and grown on the top of said texture.

  (Original) The serriconductor device of claim 1, further comprising buffer layer grown
- in between said epitavial layer and said texture.
  (Original) The semiconductor device of claim. i, wherein said texture comprising wells

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- and wells.

  (Original) The semiconductor device of chim 3, wherein the width of said walls is in a range of narometers to crimoneters.
- (Origani) The semiconductor device of claim 3, whereis the depth of said well is in a carge of nanometers to micrometers.
- (Currently amended)The semiconductor device of claim 3, wherein said walls having a skape of rectangular.
- (Origianl) The semiconductor device of claim 6, wherein the dimension of said wells is in
  the range of narometers to micrometers.
   (currently amended) The semiconductor device of claim 1, wherein said opinaxial layer of
- [Delation] A semiconductor device, comprising

said semiconductor device enrits hight

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second texture

a substrate with first texture on one of its two surfaces,

a first epitaxial layer comprising first active tayer and grown on the top of said first

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a second texture eithed on the top surface of said first epitaxial layer,

a second epitaxisi laye: comprising second active layer and grown on the top of said

10. [Debtion] The semiconductor device of claim 9, further comprising first huffer layer grown in between said first ephanal layer and said first texture of said substrate, and a second buffer layer grown in between said second epitaxial layer and said second texture of said first epinaxial layer.

1. [Deleticn] The semiconductor device of claim 9, wherein both said first texture and said second leature acouptions wells and walls.

12. Deletion The semiconcustor davice of claim 11, wherein the width of said walls is in a range of nanome act to mixtureters.

3. [Deletion] The semiconductor device of claim 11, where n the depth of said wells is in a range of nanometers to micromoters.

14. [Delation]The semicenductor device of claim 11, wherein said wells frave the shape of said semiconductor device.

15. [Deletion]The seminontheror device of claim 11, wherein the dimension of said wells in it the range of nanomoleus to missemeless.

16. [Deletion] he seniconductor device of claim 9, wherein said suisstate emits light.

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